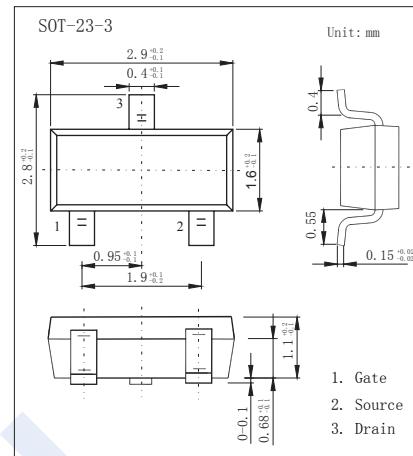
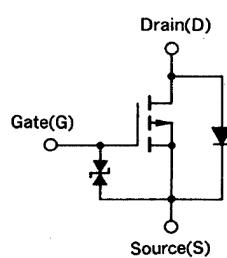


## P-Channel MOSFET

## 2SJ204

## ■ Features

- $V_{DS} (V) = -30V$
- $I_D = -200mA$
- $R_{DS(on)} < 8\Omega$  ( $V_{GS} = -10V$ )
- $R_{DS(on)} < 13\Omega$  ( $V_{GS} = -4V$ )
- Complementary to 2SK1582

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	-200	mA
Pulsed Drain Current (Note.1)	$I_{DM}$	-400	
Power Dissipation	$P_D$	200	mW
Junction Temperature	$T_J$	150	$^\circ C$
Operating Temperature	$T_{opt}$	-55 to 80	
Junction Storage Temperature Range	$T_{stg}$	-55 to 150	

Note.1:  $PW \leq 10ms$ , Duty Cycle  $\leq 50\%$

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D = -250\mu A, V_{GS}=0V$	-30			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-30V, V_{GS}=0V$			-1	$\mu A$
Gate-Body leakage current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 20V$			$\pm 1$	$\mu A$
Gate Cut off Voltage	$V_{GS(off)}$	$V_{DS}=-5V, I_D=-1\mu A$	-1.4	-2.4		V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4V, I_D=-10mA$			13	$\Omega$
		$V_{GS}=-10V, I_D=-10mA$			8	
Forward Transconductance	$g_{FS}$	$V_{DS}=-5V, I_D=-10mA$	20			$mS$
Input Capacitance	$C_{iss}$	$V_{GS}=0V, V_{DS}=-10V, f=1MHz$		27		$pF$
Output Capacitance	$C_{oss}$			27		
Reverse Transfer Capacitance	$C_{rss}$			6		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS(on)}=-4V, V_{DS}=-5V, I_D=-0.3A, R_L=1.5\Omega, R_{GEN}=10\Omega$		120		ns
Turn-On Rise Time	$t_r$			240		
Turn-Off Delay Time	$t_{d(off)}$			135		
Turn-Off Fall Time	$t_f$			210		

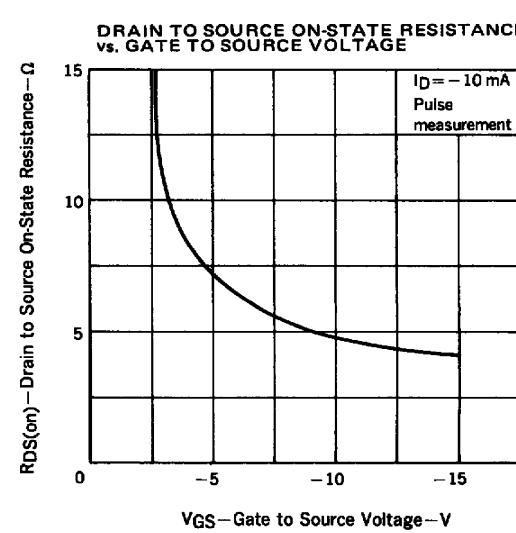
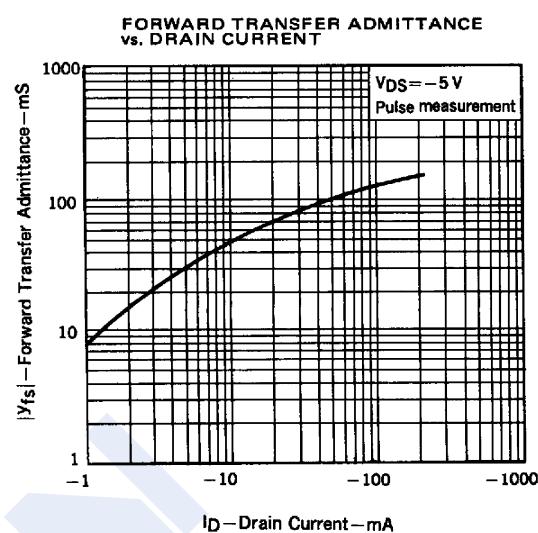
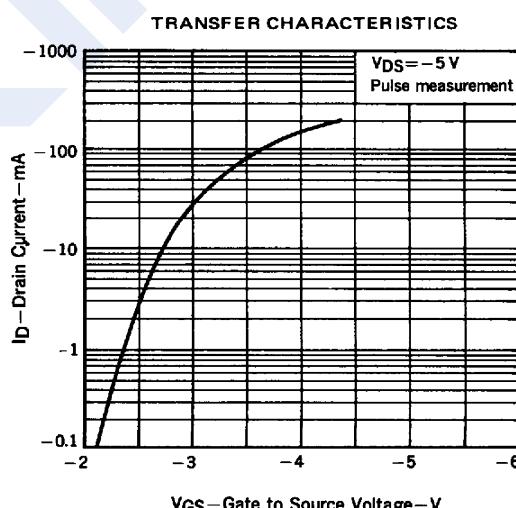
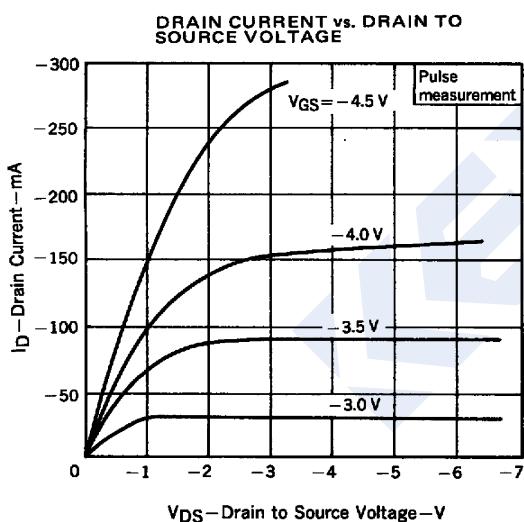
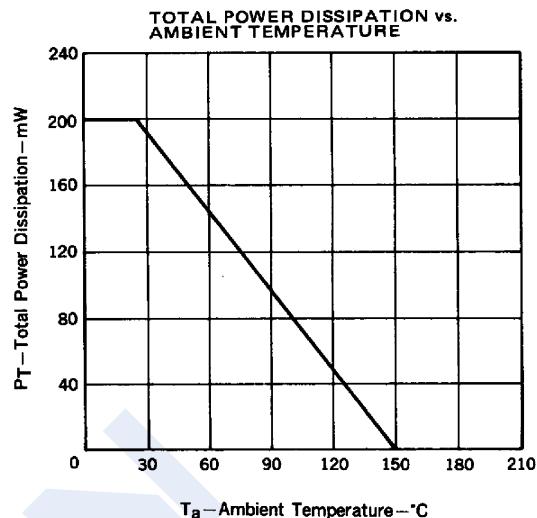
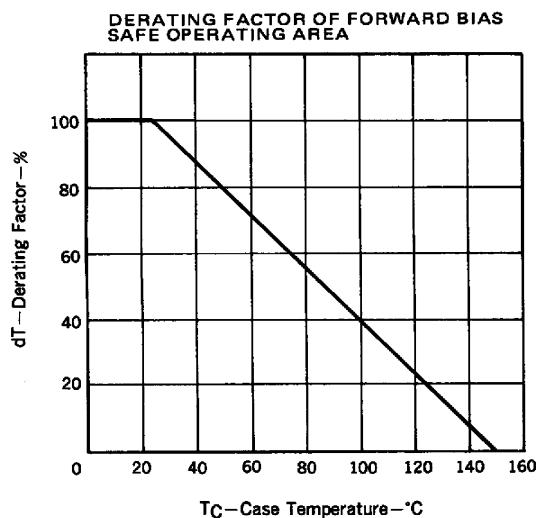
## ■ Marking

Marking	H15
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## P-Channel MOSFET

2SJ204

## ■ Typical Characteristics



## P-Channel MOSFET

### 2SJ204

#### ■ Typical Characteristics

